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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Ichio YUDASAKA, Mitsutoshi MIYASAKA,  
Piero MIGLIORATO

Application No.: U.S. National Stage of PCT/GB01/00009

Filed: September 7, 2001

Docket No.: 110553

For: METHOD OF MANUFACTURING A THIN-FILM TRANSISTOR

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office  
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 3, 7-9 and 11-13 as follows:

*At*  
3. (Amended) A method of manufacturing a thin-film transistor according to Claim 1,  
characterized in that a process of introducing said impurity to said channel region is carried  
out by injecting the impurity from a surface side of said channel region.

*Ar*  
7. (Amended) A method of manufacturing a thin-film transistor according to Claim 3,  
characterized in that an average projected range of the impurity in said process of introducing  
an impurity is from the center in the direction of thickness of said channel region to an  
interface between the channel region and the gate insulating film.

*int  
cont*  
8. (Amended) A method of manufacturing a thin-film transistor according to Claim 3,  
characterized in that an average projected range of the impurity in said process of introducing